



T0820H-8K 8A TRIAC

Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.8)	V_{pp}	3	kV
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ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33$	- -	MAX.	20	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=150$ $R_L=3.3k$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	40	mA
				55	
I_H	$I_T=100mA$		MAX.	30	mA
dV/dt	$V_D=540V$ Gate Open $T_j=150$		MIN.	800	V/ μs
$(dI/dt)_c$	$(dV/dt)_c=20V/\mu s$, $T_j=150$		MIN.	3	A/ms
t_{on}	$I_G=40mA$ $I_A=200mA$ $I_R=20mA$ $T_j=2$				

ORDERING INFORMATION 1

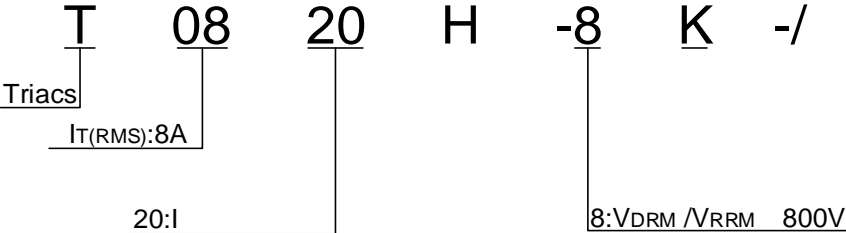


FIG.1: Maximum power dissipation versus RMS on-state current

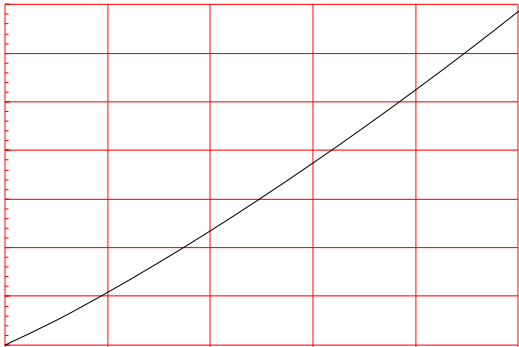


FIG.2: RMS on-state current versus case temperature



FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

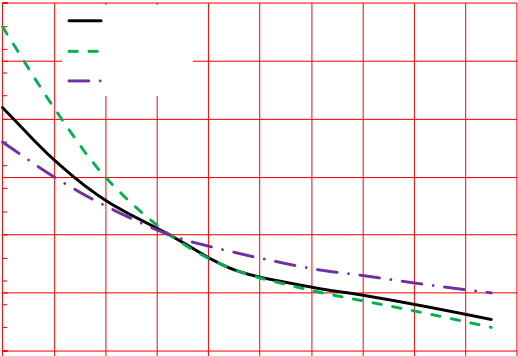
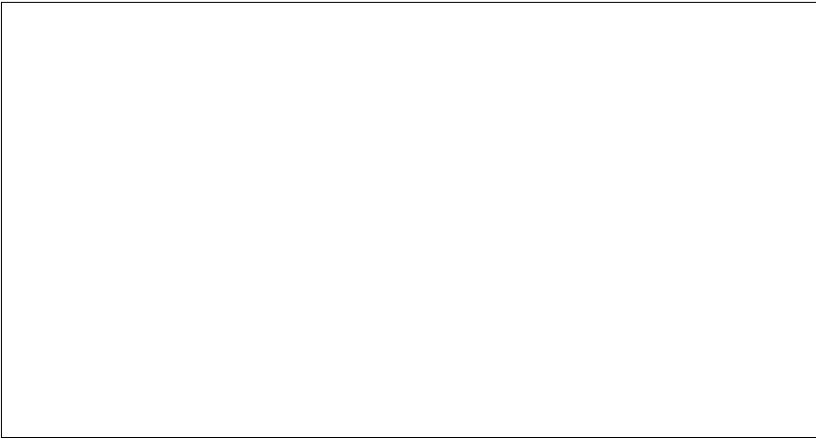


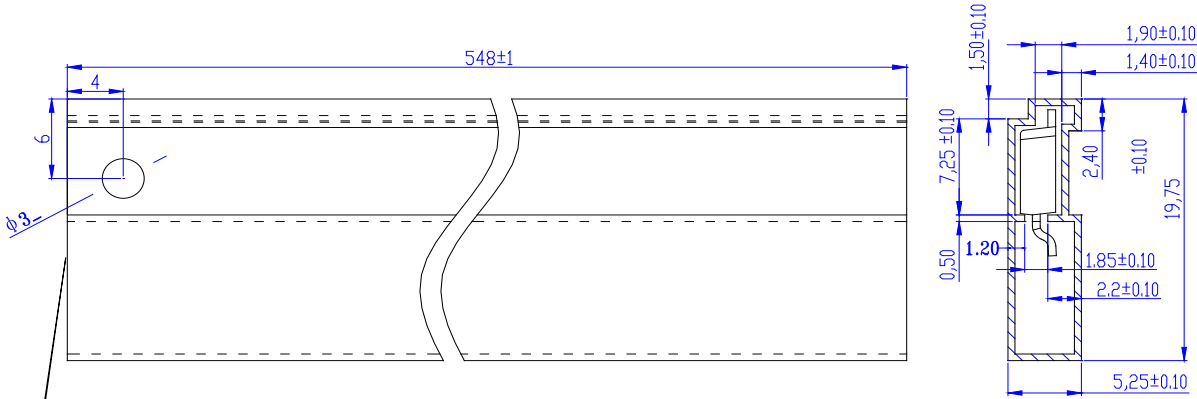
FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards

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DELIVERY MODE



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